(X) Original

DECLARATION AND POWER OF ATTORNEY FOR U.S. PATENT APPLICATION

() Supplemental

() Substitute

() PCT

() Design

tle: POSITIVE-WORKING	PHOTORESIST COMPOSITION		
and with amendments through) the specification in International A on (if a	s Serial No filed (if applicable), or pplication No. PCT/ applicable).	, filed	
fined in Title 37, Code of Federal Interest in Title 37, Code of Feder	the Patent and Trademark Office all in Regulations, §1.56. Title 35, United States Code, §119 (and god below and have also identified below	§172 if this application is for a Design	n) of any application(
COUNTRY	APPLICATION NO.	DATE OF FILING	PRIORITY CLAIMED
Japan	11-74097	March 18, 1999	Yes
Japan			
Japan			

And I hereby appoint Michael R. Davis, Reg. No. 25,134; Matthew M. Jacob, Reg. No. 25,154; Jeffrey Nolton, Reg. No. 25,408; Warren M. Cheek, Jr., Reg. No. 33,367; Nils E. Pedersen, Reg. No. 33,145 and Charles R. Watts, Reg. No. 33,142, who together constitute the firm of WENDEROTH, LIND & PONACK, L.L.P., attorneys to prosecute this application and to transact all business in the U.S. Patent and Trademark Office connected therewith.

I hereby authorize the U.S. attorneys named herein to accept and follow instructions from

Agata Patent Office
as to any action to be taken in the U.S. Patent and Trademark Office regarding this application without direct communication between the U.S. attorneys and myself. In the event of a change in the persons from whom instructions may be taken, the U.S. attorneys named herein will be so notified by me.

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I further declare that all statements made herein of my own knowledge are true, and that all statements on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

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3rd Inventor Jakno	Date (February 22 2000
3rd Inventor Taku NAKAO 4th Inventor Kazuyuki NITTA Satoshi MAEMORI Taku Qakao Kaguguki hitta	Date February . 28, 2000
5th Inventor	Date
6th Inventor	Date
7th Inventor	Date
The above application may be more particularly identified as follow	vs:
U.S. Application Serial No.	Filing Date
Applicant Reference Number	Atty Docket No.
Title of Invention	

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of :

Kazufumi SATO et al. :

Serial No. New :

Filed

POSITIVE-WORKING PHOTORESIST : COMPOSITION

Rule 132 DECLARATION

P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

I, the undersigned Kazuyuki NITTA, do hereby declare:

THAT I am an employee of Tokyo Ohka Kogyo Co., Ltd., Japan, the assignee of the above-identified United States patent application, since April, 1990, being engaged in the research and development works relative to the chemical-amplification positive-working photoresist compositions and other related products of the company;

THAT, I am one of the joint inventors in the above-identified pending United States patent application, which is a divisional application from Serial No. 10/114,258 filed April 3, 2002, which in turn is a divisional application of Serial No. 09/521,205 filed March 8, 2000, I have full acquaintance with the subject matter of the above-identified pending application and have caused the comparative experiments described below either by myself or under my

direct supervision; and

THAT I have a good knowledge of the English language and have read and understood the application papers and the prosecution history of the antecedent applications as well as the Examiner's references cited therein.

COMPARATIVE EXPERIMENTS

I. Object of experiments

While claim 1 of the above-identified patent application requires that the ratio of the maximum weight-average molecular weight Mw_{max} to the minimum weight-average molecular weight Mw_{min} in the two resinous ingredients combined as the component (A) is smaller than 1.5, the object of the following comparative experiments is to demonstrate the significance of this limitation on the ratio as a characteristic parameter having great influences on the performance of the photoresist composition by conducting experiments using resinous ingredients having different values of this ratio.

II. Experimental procedures and results

Experiment 1 (comparative).

A resinous ingredient as the component (A) having a Mw_{max}/Mw_{min} ratio of 1.6 was prepared as a 30:70 by weight combination of a first mixture of a polyhydroxystyrene resin having a weight-average molecular weight of 16000, of which 45% by moles of the hydroxyl hydrogen atoms were substituted by tert-butoxycarbonyl groups, and a polyhydroxystyrene resin having a weight-average molecular weight of 16000, of which 20% by moles of the hydroxyl hydrogen atoms were substituted by tert-butoxycarbonyl groups, in a mixing ratio of 65:35 by weight and a second resin mixture of a polyhydroxystyrene

resin having a weight-average molecular weight of 10000, of which 45% by moles of the hydroxyl hydrogen atoms were substituted by 1-ethoxyethyl groups, and a polyhydroxystyrene resin having a weight-average molecular weight of 10000, of which 25% by moles of the hydroxyl hydrogen atoms were substituted by 1-ethocyethyl groups, in a mixing ratio of 75:25.

A positive-working photoresist composition was prepared by dissolving, in 490 parts by weight of propyleneglycol monomethyl ether, 100 parts by weight of the above-prepared component (A) having a Mw_{max}/Mw_{min} ratio of 1.6, 7 parts by weight of bis(cyclohexylsulfonyl) diazomethane as the component (B), 0.1 part by weight of triethylamine and 0.5 part by weight of salicylic acid as an additive followed by filtration of the solution through a membrane filter of 0.2 μm pore diameter.

The thus prepared photoresist solution was subjected to the evaluation tests for the testing items (1) to (5) in the same manner as in the application to give the following results:

- (1) 12 mJ/cm² of the photosensitivity;
- (2) grade A of the cross sectional profile of the patterned resist layer;
- (3) 0.18 μm of the pattern resolution;
- (4) 2060 per wafer of the surface defects, and
- (5) grade A of the heat resistance.

Experiment 2 (comparative)

The experimental procedure was substantially the same as in Experiment 1 described above except that the component (A) having a Mw_{max}/Mw_{min} ratio of 1.8 instead of 1.6 was a 30:70 by weight combination of a first resin mixture consisting of a polyhydroxystyrene resin having a weight-average molecular weight of 9000, of which 45% by moles of the hydroxyl hydrogen

atoms were substituted by tert-butoxycarbonyl groups, and a polyhydroxystyrene resin having a weight-average molecular weight of 9000, of which 20% by moles of the hydroxyl hydrogen atoms were substituted by tert-butoxycarbonyl groups, in a mixing ratio of 65:35 by weight and a second resin mixture consisting of a polyhydroxystyrene resin having a weight-average molecular weight of 5000, of which 45% by moles of the hydroxyl hydrogen atoms were substituted by 1-ethoxyethyl groups, and a polyhydroxystyrene resin having a weight-average molecular weight of 5000, of which 25% by moles of the hydroxyl hydrogen atoms were substituted by 1-ethoxyethyl groups, in a mixing ratio of 75:25 by weight. The results of the evaluation tests for the testing items (1) to (5) were as follows:

- (1) 12 mJ/cm² of the photosensitivity;
- (2) grade A of the cross sectional profile of the patterned resist layer;
- (3) 0.18 μm of the pattern resolution;
- (4) 3200 per wafer of the surface defects, and
- (5) grade A of the heat resistance.

Experiment 3 (inventive)

The experimental procedure was substantially the same as in Experiment 1 described above except that the component (A) of the photoresist composition having a Mwmax/Mwmin ratio of 1.3 was a 30:70 by weight combination of a first resin mixture consisting of a polyhydroxystyrene resin having a weight-average molecular weight of 13000, of which 45% by moles of the hydroxyl hydrogen atoms were substituted by tert-butoxycarbonyl groups, and a polyhydroxystyrene resin having a weight average molecular weight of 13000, of which 20% by moles of the hydroxyl hydrogen atoms were substituted by tert-butoxycarbonyl groups, in a mixing ratio of 60:40 by weight and a second resin mixture consisting of a polyhydroxystyrene

resin having a weight-average molecular weight of 10000, of which 45% by moles of the hydroxyl hydrogen atoms were substituted by 1-ethoxyethyl groups, and a polyhydroxystyrene resin having a weight average molecular weight of 10000, of which 25% by moles of the hydroxyl hydrogen atoms were substituted by 1-ethoxcyethyl groups, in a mixing ratio of 70:30 by weight. The results of the evaluation tests of the photoresist composition for the testing items (1) to (5) were as follows:

- (1) 12 mJ/cm² of the photosensitivity;
- (2) grade A of the cross sectional profile of the patterned resist layer;
- (3) 0.17 μm of the pattern resolution;
- (4) 9 per wafer of the surface defects, and
- (5) grade A of the heat resistance.

Conclusion

As is clearly understood from the above-described results of the comparative experiments, the claimed upper limit of 1.5 for the Mw_{max}/Mw_{min} ratio of the resinous ingredients constituting the component (A) of the photoresist composition is critical on the quality of the patterned resist layer formed from the photoresist composition in respect of the pattern resolution and, in particular, the number of surface defects with so great differences between Experiment 3 (inventive) and Experiment 1 or 2 (comparative).

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title

18 of the United States Code and that such willful false statements may jeopardize the validity of any application or any patent issued thereon.

Date: October 22, 2003

Kazuyuki NITTA